

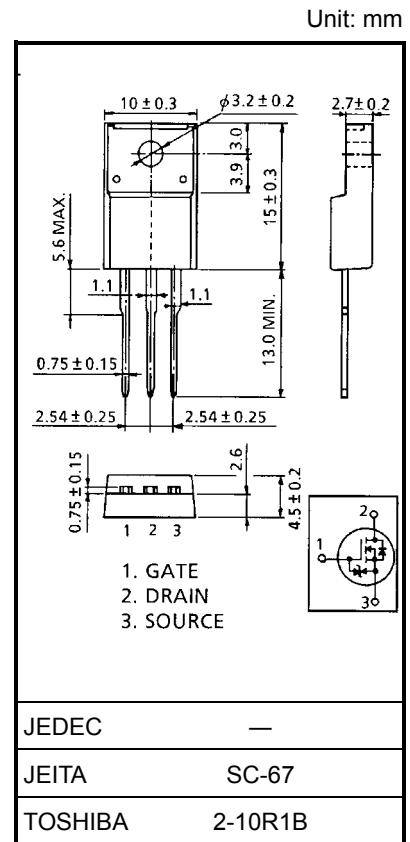
# 2SK2543

## Switching Regulator Applications

- Low drain-source ON resistance :  $R_{DS(ON)} = 0.75 \Omega$  (typ.)
- High forward transfer admittance :  $|Y_{fs}| = 7.0 S$  (typ.)
- Low leakage current :  $I_{DSS} = 100 \mu A$  (max) ( $V_{DS} = 500 V$ )
- Enhancement-mode :  $V_{th} = 2.0 \sim 4.0 V$  ( $V_{DS} = 10 V, I_D = 1 mA$ )

## Maximum Ratings ( $T_a = 25^\circ C$ )

| Characteristics                                |                | Symbol    | Rating   | Unit       |
|--|----------------|-----------|----------|------------|
| Drain-source voltage                           |                | $V_{DSS}$ | 500      | V          |
| Drain-gate voltage ( $R_{GS} = 20 k\Omega$ )   |                | $V_{DGR}$ | 500      | V          |
| Gate-source voltage                            |                | $V_{GSS}$ | $\pm 30$ | V          |
| Drain current                                  | DC (Note 1)    | $I_D$     | 8        | A          |
|  | Pulse (Note 1) | $I_{DP}$  | 32       | A          |
| Drain power dissipation ( $T_c = 25^\circ C$ ) |                | $P_D$     | 40       | W          |
| Single pulse avalanche energy (Note 2)         |                | $E_{AS}$  | 312      | mJ         |
| Avalanche current                              |                | $I_{AR}$  | 8        | A          |
| Repetitive avalanche energy (Note 3)           |                | $E_{AR}$  | 4        | mJ         |
| Channel temperature                            |                | $T_{ch}$  | 150      | $^\circ C$ |
| Storage temperature range                      |                | $T_{stg}$ | -55~150  | $^\circ C$ |



Weight: 1.9 g (typ.)

## Thermal Characteristics

| Characteristics                        | Symbol         | Max   | Unit           |
|--|----------------|-------|----------------|
| Thermal resistance, channel to case    | $R_{th(ch-c)}$ | 3.125 | $^\circ C / W$ |
| Thermal resistance, channel to ambient | $R_{th(ch-a)}$ | 62.5  | $^\circ C / W$ |

Note 1: Please use devices on condition that the channel temperature is below  $150^\circ C$ .

Note 2:  $V_{DD} = 90 V, T_{ch} = 25^\circ C$  (initial),  $L = 8.3 mH, R_G = 25 \Omega, I_{AR} = 8 A$

Note 3: Repetitive rating; Pulse width limited by maximum channel temperature.

This transistor is an electrostatic sensitive device.  
Please handle with caution.

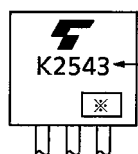
## Electrical Characteristics (Ta = 25°C)

| Characteristics                                 |               | Symbol        | Test Condition  | Min                                       | Typ. | Max      | Unit          |
|---|---------------|---------------|---|---|------|----------|---------------|
| Gate leakage current                            |               | $I_{GSS}$     | $V_{GS} = \pm 25\text{ V}, V_{DS} = 0\text{ V}$   | —   | —    | $\pm 10$ | $\mu\text{A}$ |
| Gate-source breakdown voltage                   |               | $V_{(BR)GSS}$ | $I_G = \pm 10\ \mu\text{A}, V_{GS} = 0\text{ V}$  | $\pm 30$                                  | —    | —        | V             |
| Drain cut-off current                           |               | $I_{DSS}$     | $V_{DS} = 500\text{ V}, V_{GS} = 0\text{ V}$  | —   | —    | 100      | $\mu\text{A}$ |
| Drain-source breakdown voltage                  |               | $V_{(BR)DSS}$ | $I_D = 10\text{ mA}, V_{GS} = 0\text{ V}$   | 500                                       | —    | —        | V             |
| Gate threshold voltage                          |               | $V_{th}$      | $V_{DS} = 10\text{ V}, I_D = 1\text{ mA}$   | 2.0                                       | —    | 4.0      | V             |
| Drain-source ON resistance                      |               | $R_{DS(ON)}$  | $V_{GS} = 10\text{ V}, I_D = 4\text{ A}$  | —   | 0.75 | 0.85     | $\Omega$      |
| Forward transfer admittance                     |               | $ Y_{fs} $    | $V_{DS} = 10\text{ V}, I_D = 4\text{ A}$  | 3.5                                       | 7.0  | —        | S             |
| Input capacitance                               |               | $C_{iss}$     | $V_{DS} = 10\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$   | —   | 1300 | —        | pF            |
| Reverse transfer capacitance                    |               | $C_{rss}$     |   | —   | 130  | —        |               |
| Output capacitance                              |               | $C_{oss}$     |   | —   | 400  | —        |               |
| Switching time                                  | Rise time     | $t_r$         | <p><math>I_D = 4\text{ A}</math><br/><math>V_{GS} = 10\text{ V}, 0\text{ V}</math><br/><math>R_L = 50\ \Omega</math><br/><math>V_{DD} = 200\text{ V}</math></p> | —   | 26   | —        | ns            |
|   | Turn-on time  | $t_{on}$      |   | —   | 45   | —        |               |
|   | Fall time     | $t_f$         |   | —   | 40   | —        |               |
|   | Turn-off time | $t_{off}$     |   | Duty $\leq 1\%$ , $t_w = 10\ \mu\text{s}$ | —    | 140      |               |
| Total gate charge (Gate-source plus gate-drain) |               | $Q_g$         | $V_{DD} \approx 400\text{ V}, V_{GS} = 10\text{ V}, I_D = 8\text{ A}$   | —   | 30   | —        | nC            |
| Gate-source charge                              |               | $Q_{gs}$      |   | —   | 17   | —        |               |
| Gate-drain ("miller") charge                    |               | $Q_{gd}$      |   | —   | 13   | —        |               |

## Source-Drain Ratings and Characteristics (Ta = 25°C)

| Characteristics                           | Symbol    | Test Condition                              | Min | Typ. | Max  | Unit          |
|---|-----------|---|-----|------|------|---------------|
| Continuous drain reverse current (Note 1) | $I_{DR}$  | —   | —   | —    | 8    | A             |
| Pulse drain reverse current (Note 1)      | $I_{DRP}$ | —   | —   | —    | 32   | A             |
| Forward voltage (diode)                   | $V_{DSF}$ | $I_{DR} = 8\text{ A}, V_{GS} = 0\text{ V}$  | —   | —    | -1.7 | V             |
| Reverse recovery time                     | $t_{rr}$  | $I_{DR} = 8\text{ A}, V_{GS} = 0\text{ V}$  | —   | 1200 | —    | ns            |
| Reverse recovery charge                   | $Q_{rr}$  | $dI_{DR} / dt = 100\text{ A} / \mu\text{s}$ | —   | 10   | —    | $\mu\text{C}$ |

## Marking

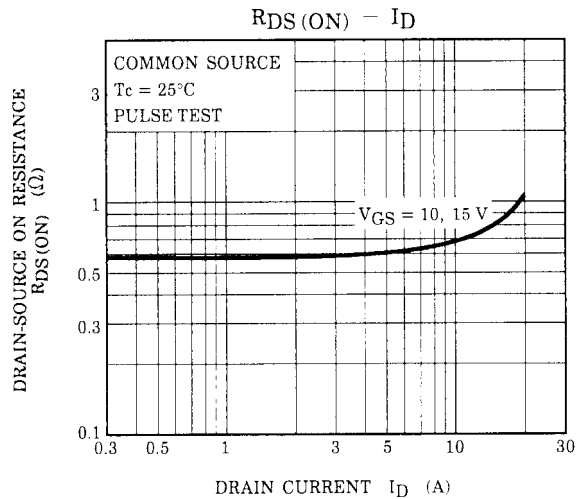
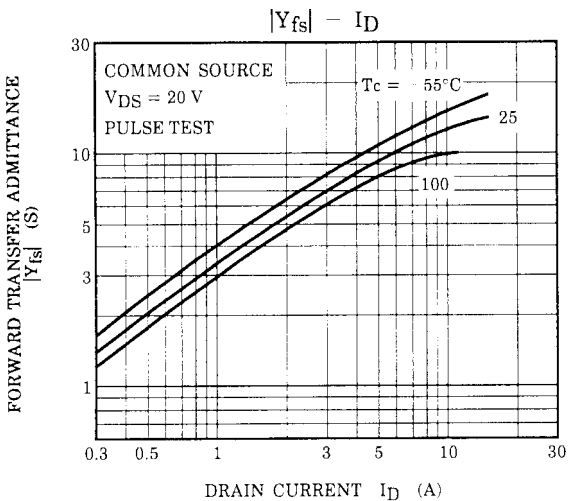
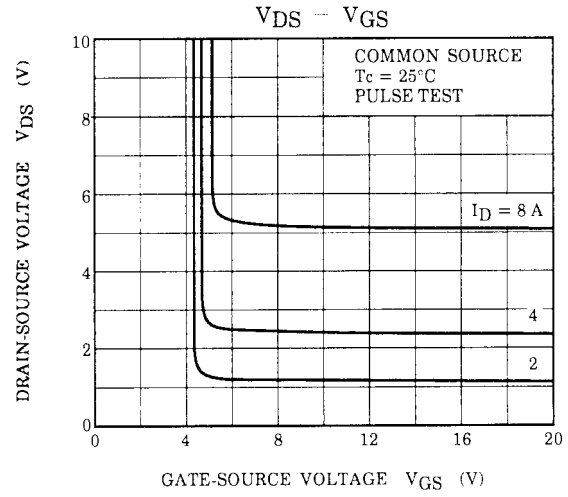
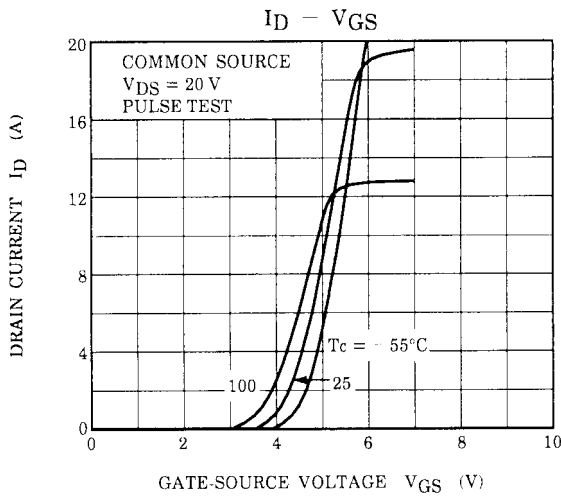
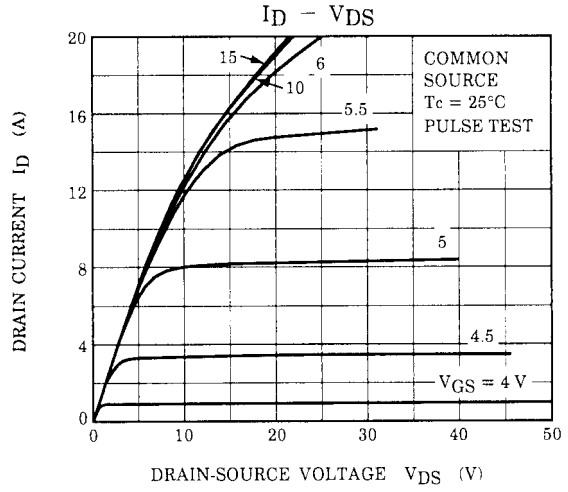
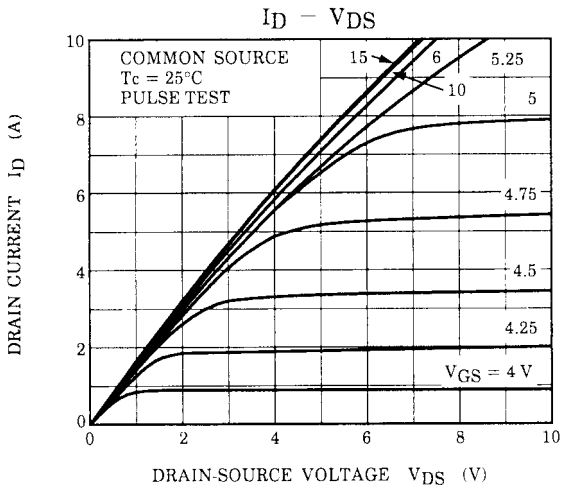


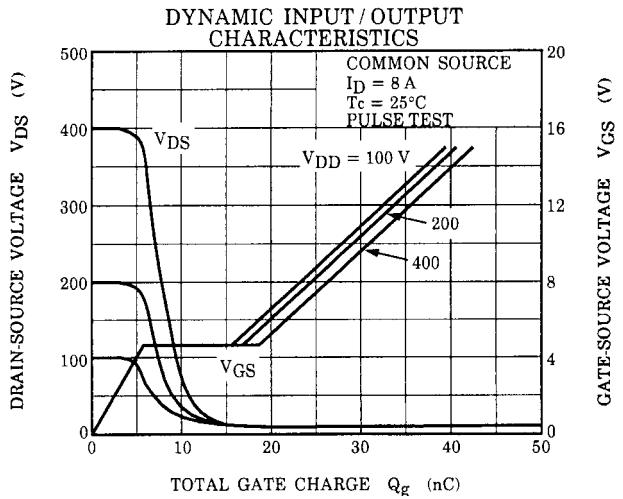
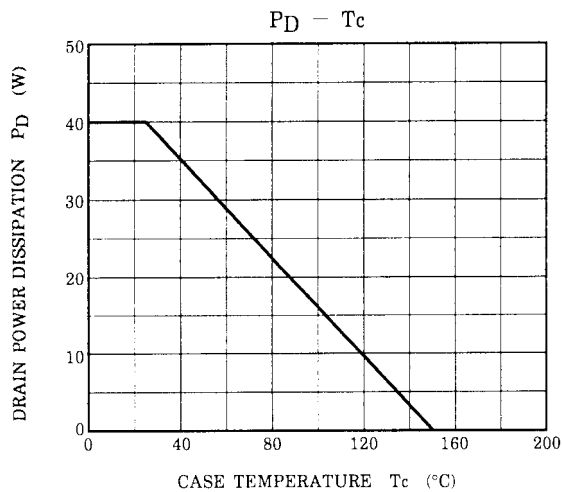
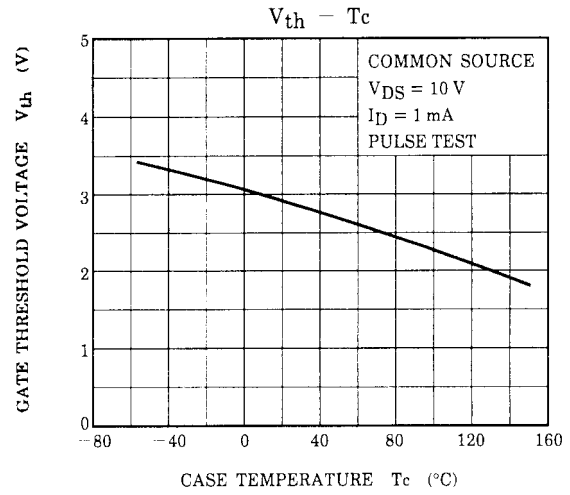
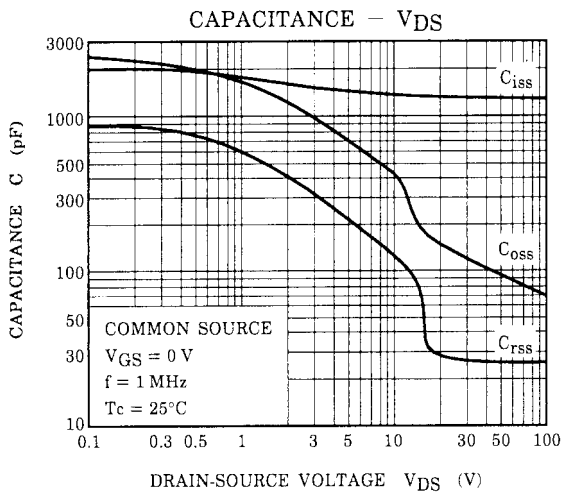
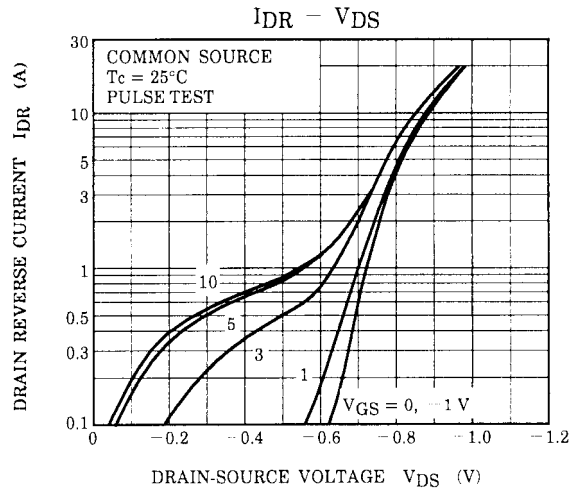
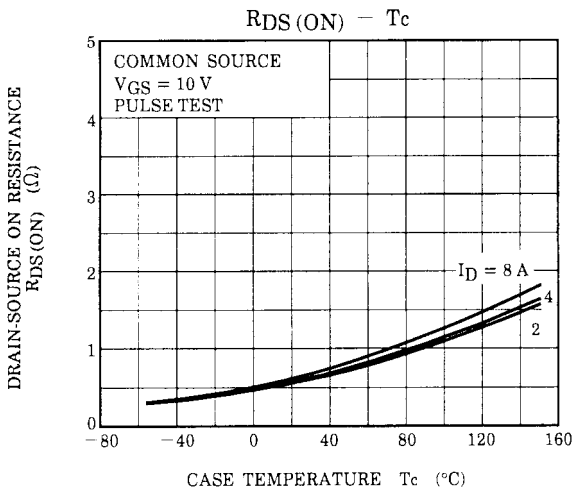
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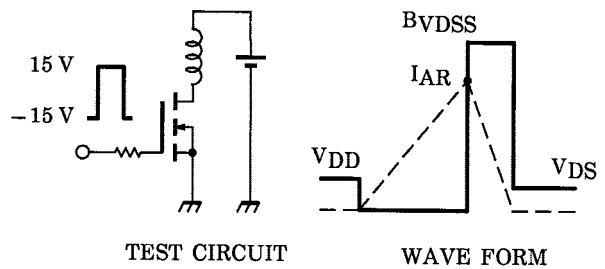
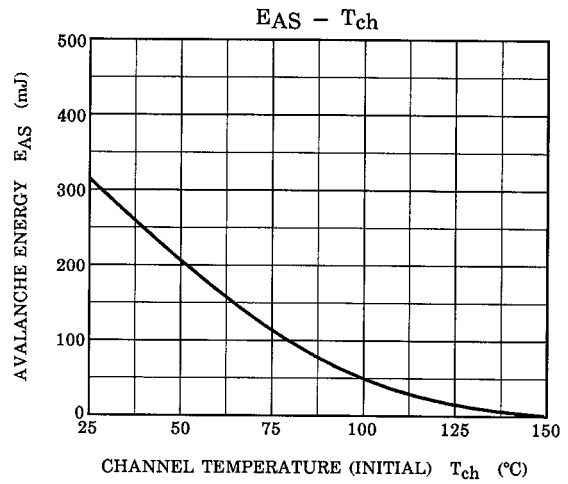
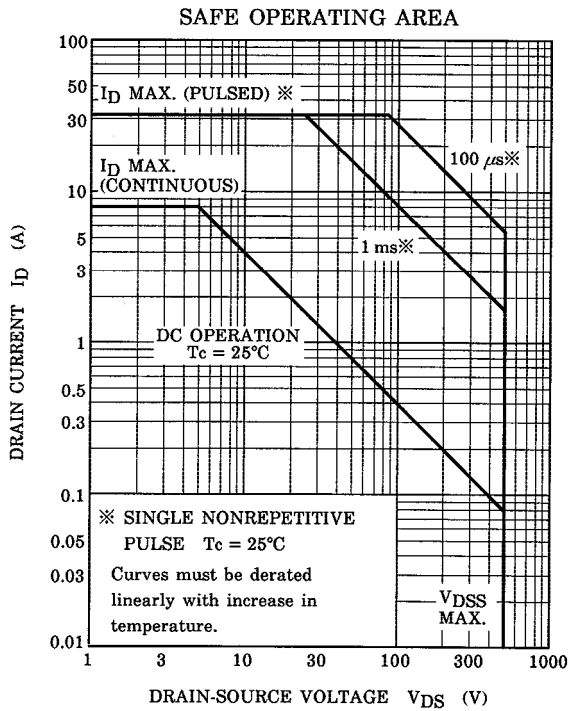
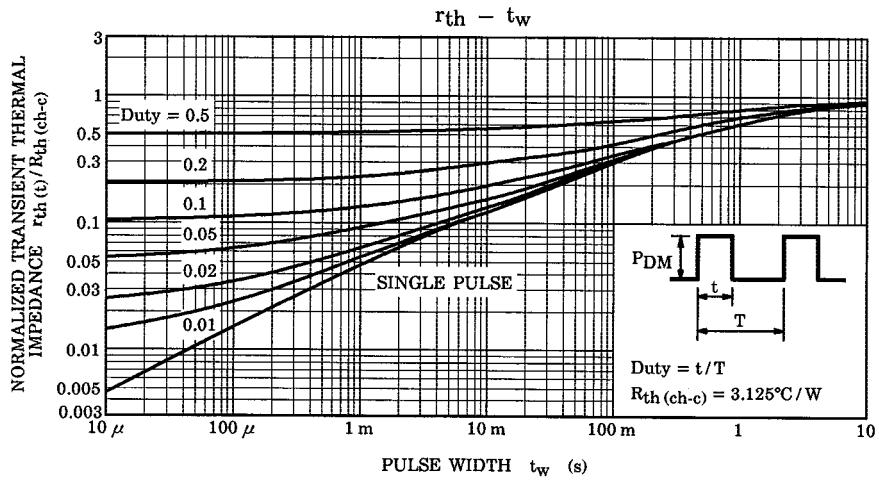
※ Lot Number

□ □ — Month (Starting from Alphabet A)

— Year (Last Number of the Christian Era)







$R_G = 25 \Omega$   
 $V_{DD} = 90 \text{ V}, L = 8.3 \text{ mH}$

$$E_{AS} = \frac{1}{2} \cdot L \cdot I^2 \cdot \left( \frac{BVDSS}{BVDSS - V_{DD}} \right)$$

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